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In re Application of

Ken INOUE et al.

Serial No.: 09/667,706

Group Art Unit: 2811

Filed: September 22, 2000

Examiner: Douglas W. Owens

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Honorable Commissioner of Patents  
Washington, D.C. 20231

**SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111**

Sir:

In supplement to the Amendment filed herein on April 17, 2002, and in further response to the Office Action dated January 17, 2002, please amend the above-identified application as follows:

**IN THE SPECIFICATION:**

**Please amend the specification to read as follows:**

On page 12, paragraph 3 starting on line 18 was amended as follows:

B - - What distinguishes the present invention from the conventional techniques the most is the fact that, even in the memory cell region of the DRAM section, there are formed the S/D regions with a high dopant concentration defined as  $n^+$ . When silicide is formed on the S/D regions with such a high dopant concentration, good ohmic contacts can be formed. Further, because the junction becomes deeper, the junction leakage current is hardly generated even if silicide is formed over all the surfaces of the S/D regions. In contrast with this, when silicide is formed on conventional low dopant-concentration regions ( $n^-$ ), Schottky contacts are formed therebetween, which is not adequate for the purpose of achieving lower resistance. - -

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